

#### **INCHANGE SEMICONDUCTOR**

## iscN-Channel MOSFET Transistor

### **TK17A65W, ITK17A65W**

#### FEATURES

- Low drain-source on-resistance:  $R_{DS}(ON) = 0.2\Omega$
- Enhancement mode: Vth = 2.5 to 3.5V (VDs = 10 V, ID=0.9mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRITION

Switching Voltage Regulators

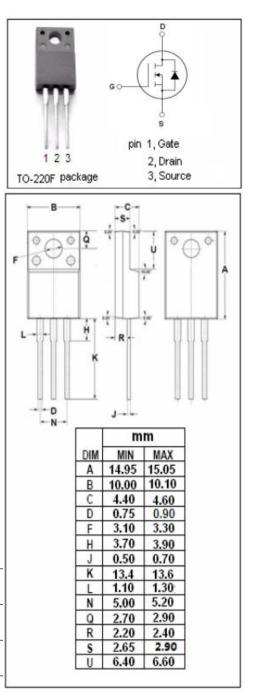
#### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| ABSOLUTE MAXIMUM RATINGS(Ta=25 C) |                                     |                                 |      |  |  |  |  |
|-----------------------------------|-------------------------------------|---------------------------------|------|--|--|--|--|
| SYMBOL                            | PARAMETER                           | VALUE                           | UNIT |  |  |  |  |
| V <sub>DSS</sub>                  | Drain-Source Voltage                | 650                             | V    |  |  |  |  |
| V <sub>GS</sub>                   | Gate-Source Voltage                 | ±30                             | V    |  |  |  |  |
| ID                                | Drain Current-Continuous 17.3       |                                 | А    |  |  |  |  |
| I <sub>DM</sub>                   | Drain Current-Single Pulsed         | rain Current-Single Pulsed 69.2 |      |  |  |  |  |
| PD                                | Total Dissipation @Tc=25°C          | 45                              | W    |  |  |  |  |
| Tj                                | Max. Operating Junction Temperature | ction Temperature 150           |      |  |  |  |  |
| T <sub>stg</sub>                  | Storage Temperature                 | -55~150                         | °C   |  |  |  |  |

#### THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                                       | МАХ  | UNIT         |
|-----------|---|------|--------------|
| Rth(ch-c) | Channel-to-case thermal resistance              | 2.78 | °C <b>/W</b> |
| Rth(ch-a) | Rth(ch-a) Channel-to-ambient thermal resistance |      | °C/W         |

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# **TK17A65W, ITK17A65W**

### **ELECTRICAL CHARACTERISTICS**

 $T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$  unless otherwise specified

| SYMBOL               | PARAMETER                      | CONDITIONS                                    | MIN | ТҮР | МАХ | UNIT |
|----------------------|--------------------------------|---|-----|-----|-----|------|
| BV <sub>DSS</sub>    | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 10mA    | 650 |     |     | V    |
| V <sub>GS</sub> (th) | Gate Threshold Voltage         | V <sub>DS</sub> = 10V; I <sub>D</sub> =0.9mA  | 2.5 |     | 3.5 | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =8.7A   |     |     | 200 | mΩ   |
| I <sub>GSS</sub>     | Gate-Source Leakage Current    | V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V    |     |     | ±1  | μA   |
| I <sub>DSS</sub>     | Drain-Source Leakage Current   | V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V  |     |     | 10  | μA   |
| V <sub>SDF</sub>     | Diode forward voltage          | I <sub>DR</sub> =17.3A, V <sub>GS</sub> = 0 V |     |     | 1.7 | V    |

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